

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

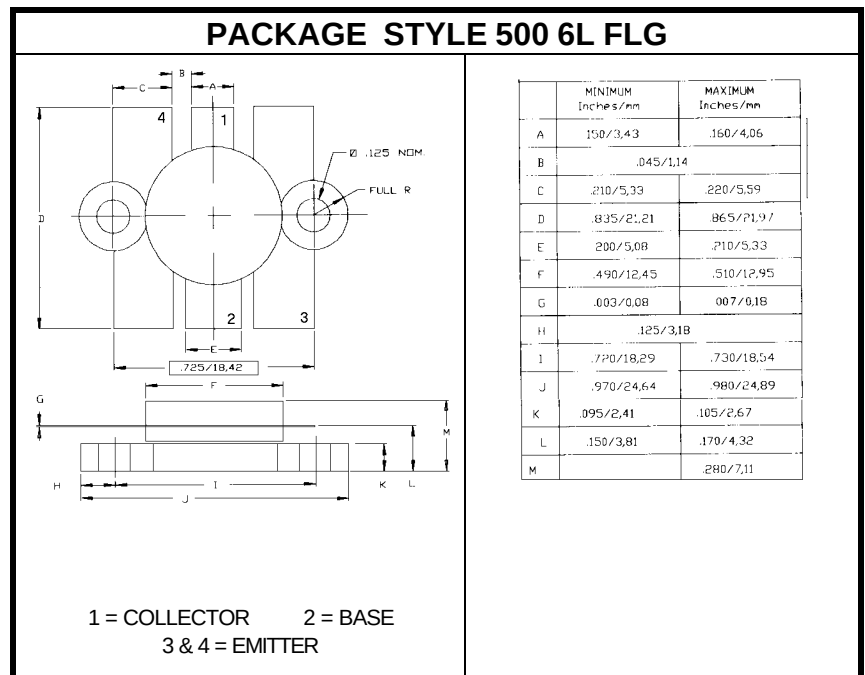
The **TPV387** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching
- Common Emitter

MAXIMUM RATINGS

I_C	16 A (CONT)
V_{CE}	35 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
q_{JC}	1.0 °C/W



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA		35			V
BV_{CER}	I _C = 100 mA	R _{BE} = 10 Ω	60			V
BV_{CBO}	I _C = 50 mA		65			V
BV_{EBO}	I _E = 20 mA		4.0			V
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A	20		100	---
C_{ob}	V _{CB} = 30 V	f = 1.0 MHz		130	150	pF
G_{PE}	V _{CC} = 28 V	P _{out} = 24 W	f = 225 MHz	13		dB
y	V _{CC} = 28 V P _{out} = 24 W	ALL PHASE ANGLES LOAD VSWR = ∞:1	f = 225 MHz	NO DEGRADATION IN OUTPUT POWER		
IMD₁	V _{CE} = 28 V VISION CARRIER = -8 dB SIDE BAND SIGNAL = -16 dB	P _{ref} = 24 W SOUND CARRIER = -7 dB I _E = 3.5 A	f = 225 MHz		-50	dB
P_{o1dB}	V _{CC} = 28 V	I _Q = 200 mA	f = 225 MHz	90		W



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